Naoya Iwamoto

List of Publications by Year
in descending order

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		1478505	1372567
16	150	6	10
papers	citations	h-index	g-index

16	16	16	150
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Radiation hardness of n-type SiC Schottky barrier diodes irradiated with MeV He ion microbeam. Nuclear Instruments & Methods in Physics Research B, 2015, 348, 233-239.	1.4	7
2	Development of diagnostic method for deep levels in semiconductors using charge induced by heavy ion microbeams. Nuclear Instruments & Methods in Physics Research B, 2015, 348, 240-245.	1.4	5
3	Defect Levels in High Purity Semi-Insulating 4H-SiC Studied by Alpha Particle Induced Charge Transient Spectroscopy. Materials Science Forum, 2014, 778-780, 289-292.	0.3	0
4	Linear energy transfer dependence of single event gate rupture in SiC MOS capacitors. Nuclear Instruments & Methods in Physics Research B, 2014, 319, 75-78.	1.4	18
5	Continuous observation of polarization effects in thin SC-CVD diamond detector designed for heavy ion microbeam measurement. Nuclear Instruments & Methods in Physics Research B, 2014, 331, 113-116.	1.4	25
6	Heavy-Ion Induced Anomalous Charge Collection From 4H-SiC Schottky Barrier Diodes. IEEE Transactions on Nuclear Science, 2013, 60, 2647-2650.	2.0	22
7	Focused Microbeam Irradiation Effects in Transmission CVD Diamond Film Detectors. Transactions of the Materials Research Society of Japan, 2013, 38, 279-282.	0.2	6
8	Single-Alpha-Particle-Induced Charge Transient Spectroscopy of the 6H-SiC ${hbox{p}}^{+}{hbox{n}}$ Diode Irradiated With High-Energy Electrons. IEEE Transactions on Nuclear Science, 2011, 58, 3328-3332.	2.0	4
9	Oxygen Ion Induced Charge in SiC MOS Capacitors Irradiated with Gamma-Rays. Materials Science Forum, 2011, 679-680, 362-365.	0.3	2
10	Charge Enhancement Effects in 6H-SiC MOSFETs Induced by Heavy Ion Strike. IEEE Transactions on Nuclear Science, 2010, , .	2.0	6
11	Reduction of Effective Carrier Density and Charge Collection Efficiency in SiC Devices Due to Radiations. , 2009, , .		3
12	Transient Response of Charge Collection by Single Ion Strike in 4H-SiC MESFETs. IEEE Transactions on Nuclear Science, 2009, 56, 3218-3222.	2.0	24
13	Decrease of Charge Collection Due to Displacement Damage by Gamma Rays in a 6H-SiC Diode. IEEE Transactions on Nuclear Science, 2007, 54, 1953-1960.	2.0	16
14	Charge Collection Efficiency of 6H-SiC P⁺N Diodes Degraded by Low-Energy Electron Irradiation. Materials Science Forum, 0, 645-648, 921-924.	0.3	7
15	Peak Degradation of Heavy-Ion Induced Transient Currents in 6H-SiC MOS Capacitors. Materials Science Forum, 0, 717-720, 469-472.	0.3	1
16	Radiation Response of Silicon Carbide Diodes and Transistors. , 0, , .		4